IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: 10/797,876 Applicant: Anthony Dip et al.

Art Unit: 2811

Title: SILICON GERMANIUM SURFACE LAYER FOR HIGH-K

DIELECTRIC INTEGRATION

Attorney Docket: TPS-007

Confirmation No.: 5070

Cincinnati, Ohio 45202 June 9, 2006

Mail Stop Amendment Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Sir

RESPONSE TO ELECTION/RESTRICTION REQUIREMENT

This paper is responsive to the Office Action mailed May 31, 2006. The Examiner has indicated that claims 1-8, 10, 11 and 13-21 are pending in the application and are subject to restriction and/or election requirement. Specifically, we understand that the Examiner has grouped the claims between Group I, claims 1-8, 10-11 and 13-20, and Group II, claim 21. Group I is directed to a method of forming a semiconductor device, and Group II is directed to a transistor device. Applicants hereby elect Group I, claims 1-8,10-11 and 13-20, directed to a method.

Examination on the merits of elected claims 1-8, 10-11 and 13-20 is respectfully requested.

Application Serial No. 10/797,876 Response dated June 9, 2006 Reply to Office Action of May 31, 2006

Respectfully submitted,

WOOD, HERRON & EVANS LLP.

By: <u>/Kristi L. Davidson/</u>
Kristi L. Davidson, Reg. No. 44,643

2700 Carew Tower 441 Vine Street Cincinnati, OH 45202 513/241-2324 (voice) 513/241-6234 (facsimile) K-DEVORD/Sresponse to Restr Req